

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1788	438/424.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 05:49
L3	602	438/435.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 06:31
L4	855	438/for.227.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 06:20
L5	317	438/for.221.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 06:40
S1	185317	han.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 12:41
S2	632	keum.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 07:46
S3	25	S1 and S2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 07:52
S5	2	"20050101092"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 07:56

EAST Search History

S9	2	"6281082".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 08:42
S11	6	"0678912"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 08:54
S14	167834	gate adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 09:01
S15	73717	contact adj hole	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 09:02
S16	85745	ion adj (implanting or implantation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 09:02
S17	227757	STI or trench adj isolation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 09:02
S18	1533	sidewall adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 09:02
S19	14	S14 and S15 and S16 and S17 and S18	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 09:30

EAST Search History

S21	138909	oxide adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 09:31
S22	18637	diffusion adj barrier	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 09:45
S24	14	S15 and S17 and S18 and S22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 09:33
S25	146	S14 and S15 and S17 and S22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 09:45
S26	11158	etch adj stop adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 09:45
S27	6088	diffusion adj barrier adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 09:45
S28	718	S26 and S27	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 09:46
S29	165	S28 and S15	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 10:38

EAST Search History

S33	2	"20020025669"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 10:21
S34	764	438/296.CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 11:53
S35	61	("5763315").URPN.	USPAT	OR	ON	2005/10/24 11:17
S36	2	"6165854".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 11:56
S37	2	"6417097".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 14:38
S38	59501	amorphous adj silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 13:39
S39	1597959	semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 13:38
S40	1118	amorphous adj silicon adj material	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 13:39
S41	854	S39 and S40	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 13:40

EAST Search History

S42	11040	n adj doped or n-doped	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 13:41
S43	44	S41 and S42	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 13:41
S44	6088	diffusion adj barrier adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 14:04
S45	146	S44 and S42	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 14:04
S46	12491	amorphous adj silicon adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 14:49
S47	11158	etch adj stop adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 14:39
S48	329	S47 and S46	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 14:45
S49	2	"6607976".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 14:47

EAST Search History

S50	356	amorphous adj silicon adj oxide adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 14:49
S51	1	amorphous adj silicon adj oxide adj barrier adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 14:58
S52	2	"5317192".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 14:50
S53	116	silicon adj oxide adj barrier adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 15:08
S54	0	doped adj oxide adj barrier adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 14:59
S55	984	oxide adj barrier adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 15:07
S56	13	S42 and S55	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 15:32
S57	17	n-doped adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 15:35

EAST Search History

S58	5	n-doped adj silicon adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 15:36
S59	1403	dongbu.as.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 18:01
S60	26782	hwang.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 18:01
S61	31	S59 and S60	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 18:02
S62	6847	noh.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 18:03
S63	7	S59 and S62	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 18:03
S64	298383	oxide adj (layer or liner or film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 18:16
S65	27	oxide adj (layer or liner or film) near4 except adj spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 18:18

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S66	813	438/296.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 19:12
S67	2	10/848982.app.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 18:37
S68	1	10/358601.app.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 18:38
S69	2	"20030227048"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 18:41
S70	2	"6756633".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 18:42
S71	0	(oxidation adj (layer or liner or film) and (substrate or wafer) and except adj spacer).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/14 08:44
S72	6253	rhodes.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 19:16
S73	31746	micron.as.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 19:16

EAST Search History

S74	345	S72 and S73	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 19:21
S75	2	oxidation adj (layer or liner or film) and (substrate or wafer) and except adj spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/14 08:45
S76	0	oxide adj (layer or liner or film) adj (substrate or wafer) near4 except adj spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/14 08:46
S77	1	(layer or liner or film) adj (substrate or wafer) near4 except adj spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/14 08:47
S78	818	438/296.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/14 08:48
S79	224023	sti or shallow adj trench adj isolation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 09:40
S80	175361	gate adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 09:40
S81	7299	S79 and S80	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 09:40

EAST Search History

S82	20273	bpsg	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 09:41
S83	1217	S81 and S82	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 09:41
S84	4610225	contact	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 09:41
S85	1172	S83 and S84	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 09:41
S86	20891	etch adj stop	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 09:41
S87	258	S85 and S86	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 09:41
S88	21420	ldd	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 09:42
S89	91	S87 and S88	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 09:46

EAST Search History

S90	8236	selective adj deposition or selectively adj (deposite or depositing)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 09:54
S91	1	S89 and S90	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 09:44
S92	189446	han.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 10:34
S93	1	(diffusion adj barrier and contact adj hole and ldd and trench and (selectively or selective)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 09:51
S94	15	diffusion adj barrier and contact adj hole and ldd and trench and (selectively or selective).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 09:54
S95	408	S79 and S90	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 10:10
S96	98	438/295.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 10:28
S97	29	han-chang.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 10:40

EAST Search History

S98	0	keum-dong.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 10:35
S99	814	S92 and cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 11:28
S100	16	10/235773.app. 10/743493.app. 10/746615.app. 10/746980.app. 10/747196.app. 10/747307.app. 10/746702.app. 10/749648.app. 10/750250.app. 10/750282.app. 10/952161.app. 10/975200.app. 10/982643.app. 11/020525.app. 11/022886.app. 11/022890.app. 11/148212.app. 11/280318.app. 11/301190.app. 11/318434.app.	US-PGPUB	OR	ON	2006/04/17 11:10
S101	19	10/235773.app. 10/743493.app. 10/746615.app. 10/746980.app. 10/747196.app. 10/747307.app. 10/746702.app. 10/749648.app. 10/750250.app. 10/750282.app. 10/952161.app. 10/975200.app. 10/982643.app. 11/020525.app. 11/022886.app. 11/022890.app. 11/148212.app. 11/280318.app. 11/301190.app. 11/318434.app. 10/318439.app. 11/318439.app. 11/319586.app. 11/319591.app. 11/319596.app. 11/319597.app. 11/320739.app. 09/105274.app. 10/201860.app. 10/751190.app. 11/319067.app.	US-PGPUB	OR	ON	2006/04/17 11:14
S102	7	08/241172.app. 08/948840.app. 08/297420.app. 08/297759.app. 08/658807.app. 10/747601.app. 10/925078.app. 11/319482.app. 11/320979.app. 08/130291.app. 11/319489.app. 08/565360.app. 08/678036.app. 08/764791.app. 08/777467.app. 09/945595.app. 11/207698.app. 10/626584.app. 11/024850.app. 11/026881.app. 11/302473.app. 11/313719.app.	US-PGPUB	OR	ON	2006/04/17 11:21

EAST Search History

S10 3	0	(gate adj electrode and (ldd or lightly adj doped adj drain) and spacer and sidewall and (sti or shallow adj trench adj isolation or device adj isolation) and oxide adj (layer or liner or film) and barrier adj (layer or liner or film) and interlayer adj dielectric adj layer). clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 11:33
S10 4	0	(gate adj electrode and (ldd or lightly adj doped adj drain) and spacer and sidewall and (sti or shallow adj trench adj isolation or device adj isolation) and oxide adj (layer or liner or film) and barrier adj (layer or liner or film) and ILD). clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 11:34
S10 5	0	(gate adj electrode and (ldd or lightly adj doped adj drain) and spacer and sidewall and (sti or shallow adj trench adj isolation or device adj isolation) and oxide adj (layer or liner or film) and barrier adj (layer or liner or film) and interlayer adj dielectric adj layer). clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 11:34
S10 6	0	(gate adj electrode and (ldd or lightly adj doped adj drain) and spacer and sidewall and (sti or shallow adj trench adj isolation or device adj isolation) and oxide adj (layer or liner or film) and barrier adj (layer or liner or film) and interlayer adj dielectric adj layer). clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 11:34
S10 7	0	(gate adj electrode and (ldd or lightly adj doped adj drain) and spacer and sidewall and (sti or shallow adj trench adj isolation or device adj isolation) and oxide adj (layer or liner or film) and barrier adj (layer or liner or film) and bpsg).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 11:34
S10 8	0	(gate adj electrode and (ldd or lightly adj doped adj drain) and spacer and sidewall and (sti or shallow adj trench adj isolation or device adj isolation) and oxide adj (layer or liner or film) and barrier adj (layer or liner or film) and insulation adj layer).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 11:35

EAST Search History

S10 9	0	(gate adj electrode and (ldd or lightly adj doped adj drain) and spacer and sidewall and (sti or shallow adj trench adj isolation or device adj isolation) and oxide adj (layer or liner or film) and barrier adj (layer or liner or film) and gap adj filling adj insulation adj layer).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 11:35
S11 0	0	(gate adj electrode and (ldd or lightly adj doped adj drain) and spacer and (sti or shallow adj trench adj isolation or device adj isolation) and oxide adj (layer or liner or film) and barrier adj (layer or liner or film) and gap adj filling adj insulation adj layer).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 11:36
S11 1	0	(gate adj electrode and (ldd or lightly adj doped adj drain) and spacer and oxide adj (layer or liner or film) and barrier adj (layer or liner or film) and gap adj filling adj insulation adj layer).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 11:36
S11 2	1	(gate adj electrode and (ldd or lightly adj doped adj drain) and spacer and oxide adj (layer or liner or film) and barrier and gap adj filling adj insulation adj layer).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 11:44
S11 3	1	gate adj electrode and (ldd or lightly adj doped adj drain) and spacer and oxide adj (layer or liner or film) and barrier and gap adj filling adj insulation adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 11:44
S11 4	878	438/400.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 14:37
S11 5	971	438/627.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 14:38
S11 6	6	("5635423" "5795823" "5904565" "5913147" "6156648").PN. OR ("6380082").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/04/17 15:14

EAST Search History

S11 7	0	(gate adj electrode and (ldd or lightly adj doped adj drain) and spacer and ion adj (implanting or implantation) and trench and oxidation adj layer and barrier and planarize and contact).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 15:24
S11 8	0	((substrate or wafer) and gate adj electrode and (ldd or lightly adj doped adj drain) and spacer and ion adj (implanting or implantation) and trench and oxidation adj layer and barrier and planarize and contact).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 15:25
S11 9	0	((substrate or wafer) and gate adj electrode and (ldd or lightly adj doped adj drain) and spacer and trench and oxidation adj layer and barrier and planarize and contact).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 15:25
S12 0	0	((substrate or wafer) and gate adj electrode and (ldd or lightly adj doped adj drain) and spacer and trench and barrier and planarize and contact).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 15:25
S12 1	0	(gate adj electrode and (ldd or lightly adj doped adj drain) and spacer and trench and barrier and planarize and contact).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 15:26
S12 2	0	(oxide adj layer and "except substrate").clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 15:26
S12 3	0	(oxidation adj layer and "except substrate").clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 15:26
S12 4	0	(oxidation adj layer and "whole substrate").clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 15:27

EAST Search History

S12 5	0	(oxidation adj layer and "entire substrate").clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 15:27
S12 6	51	(oxide adj layer and "entire substrate").clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 15:29
S12 7	13	(oxide adj layer and "whole substrate").clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 15:30
S12 8	0	(oxidation adj layer and "whole substrate").clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 15:30
S12 9	0	(oxidation adj (layer or liner or film) and "whole substrate").clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 15:30
S13 0	1	(oxidation adj (layer or liner or film) and "entire substrate").clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 15:30
S13 1	1	(gate adj oxide and gate adj electrode and (substrate or wafer) and (ldd or lightly adj doped adj drain) and spacer and trench and (oxide or oxidation) adj (layer or liner or film) and barrier and insulation adj (layer or liner or film) and contact).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 15:33
S13 2	3	(gate adj oxide and gate adj electrode and (substrate or wafer) and (ldd or lightly adj doped adj drain) and spacer and trench and (oxide or oxidation) adj (layer or liner or film) and barrier and contact).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/17 15:33

EAST Search History

S13 3	1361	438/585.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 09:14
S13 5	1726	438/424.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 09:11
S13 6	1018	438/770.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 12:42
S13 7	855	438/for.227.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 13:30
S13 8	317	438/for.221.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 12:43
S13 9	1	257/e29.2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 13:32
S14 0	697	257/e21.54.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 13:58
S14 1	538	257/e21.545.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 14:00

EAST Search History

S14 2	1655	257/e21.546.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 14:00
S14 3	841	438/296.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 13:10
S14 4	9	("5093273").URPN.	USPAT	OR	ON	2006/07/13 12:43
S14 5	301	438/267.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 13:22
S14 6	904	438/404.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 13:28
S14 7	992	257/e21.548.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 13:37
S14 8	193	438/224.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 13:37
S14 9	656	438/227.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 13:37
S15 0	3	(gate adj (oxide or insulation or dielectric) and gate adj electrode and spacer and ion adj implant\$5 and trench and oxide adj (layer or liner or film) and barrier and contact adj hole).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 13:43

EAST Search History

S15 1	5	(oxide adj (layer or liner or film) near7 except near2 spacer).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 13:45
S15 2	1	(form\$5 near4 oxide adj (layer or liner or film) near7 except near2 spacer).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 13:45
S15 3	0	(form\$5 near4 oxide adj (layer or liner or film) same except near2 spacer).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 13:45
S15 4	0	("forming an oxide layer on substrate").clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/13 14:42